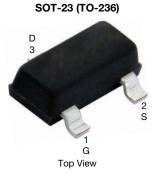
## **SQ2303ES**

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**Vishay Siliconix** 

## Automotive P-Channel 30 V (D-S) 175 °C MOSFET



FF A	TU	IRES
		nLU

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified <sup>c</sup>
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

D P-Channel MOSFET



COMPLIANT HALOGEN

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 V$	0.170			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.370			
I <sub>D</sub> (A)	-2.5			
Configuration	Single			

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2303ES (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

ABSOLUTE MAXIMUM RATINGS	$(10 - 20^{\circ})$ , unico			
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	-30	V
Gate-source voltage		V <sub>GS</sub>	± 20	
Continuous drain current	T <sub>C</sub> = 25 °C	– I <sub>D</sub>	-2.5	
Continuous drain current	T <sub>C</sub> = 125 °C		-1.5	
Continuous source current (diode conduction)		I <sub>S</sub>	-2.4	А
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	-10	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-7	
Single pulse avalanche energy		E <sub>AS</sub>	2.4	mJ
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	1.9	w
	T <sub>C</sub> = 125 °C		0.6	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	175	°C/W
Junction-to-case (drain)		R <sub>thJF</sub>	78	C/W

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. When mounted on 1" square PCB (FR-4 material)

c. Parametric verification ongoing

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	$V_{GS} = 0 V, I_D = -250 \mu A$		-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{GS}$ , $I_D$ = -250 $\mu$ A	-1.5	-2.0	-2.5	v	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V	-	-	-1	1	
	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA	
		$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	-150		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 V$	-8	-	-	Α	
Drain-source on-state resistance <sup>a</sup>		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -1.7 A	-	0.130	0.170		
	Б	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -1.7 A, T <sub>J</sub> = 125 °C	-	-	0.247	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -1.7 A, T <sub>J</sub> = 175 °C	-	-	0.288		
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -1.3 A	-	0.280	0.370		
Forward transconductance b	g <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -1.7 A		-	4	-	S	
Dynamic <sup>b</sup>		•						
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -25 V, f = 1 MHz	-	168	210	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	40	50		
Reverse transfer capacitance	C <sub>rss</sub>			-	28	35		
Total gate charge <sup>c</sup>	Qg			-	4.5	6.8		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -1.7 \text{ A}$	-	0.8	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>				1.1	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz		2.8	12.08	18.12	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	5	8		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -15 V, R <sub>L</sub> = 8.8 $\Omega$ I <sub>D</sub> $\cong$ -1.7 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 $\Omega$		-	8	12	- ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	12	18		
Fall time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-10	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	-1.5 A, V <sub>GS</sub> = 0 V	-	-0.85	-1.2	V	
					•			

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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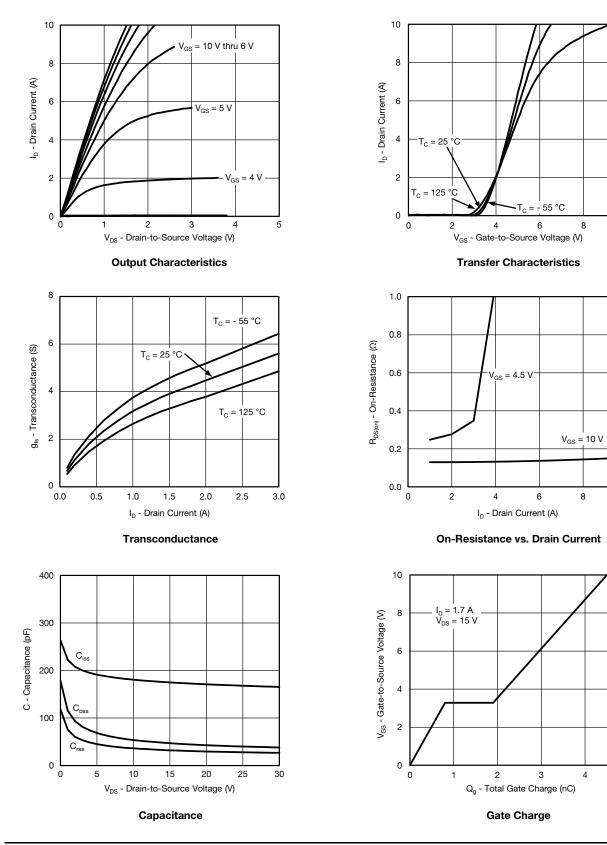


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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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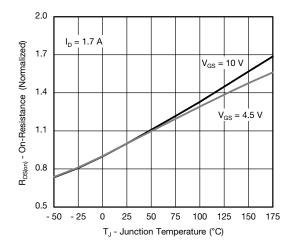
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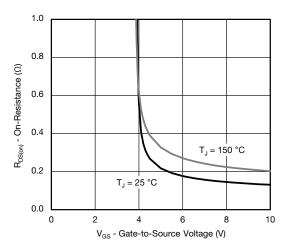
# **SQ2303ES**

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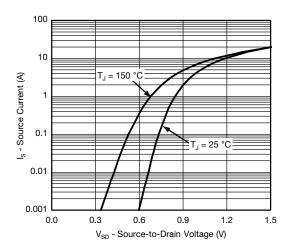
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



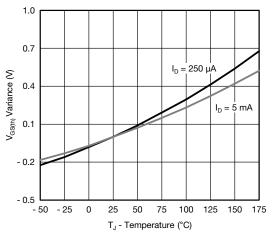
**On-Resistance vs. Junction Temperature** 



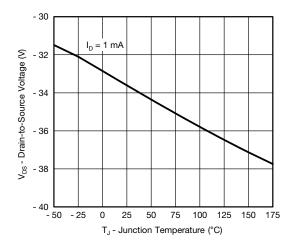
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

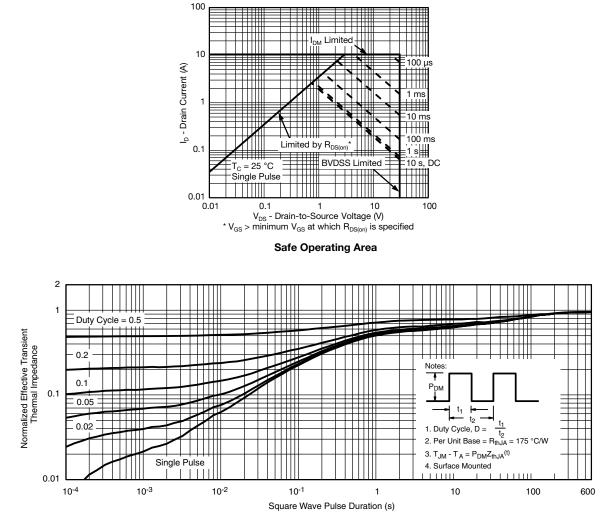
4

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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



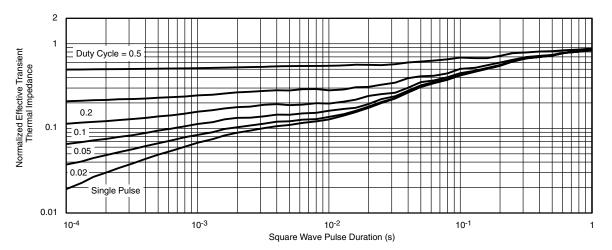
Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67023.



# Package Information

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### SOT-23 (TO-236): 3-LEAD







Dim -	MILLIN	METERS	INCHES			
	Min	Max	Min	Мах		
Α	0.89	1.12	0.035	0.044		
A <sub>1</sub>	0.01	0.10	0.0004	0.004		
A <sub>2</sub>	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E <sub>1</sub>	1.20	1.40	0.047	0.055		
е	0.95	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024		
L <sub>1</sub>	0.6	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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